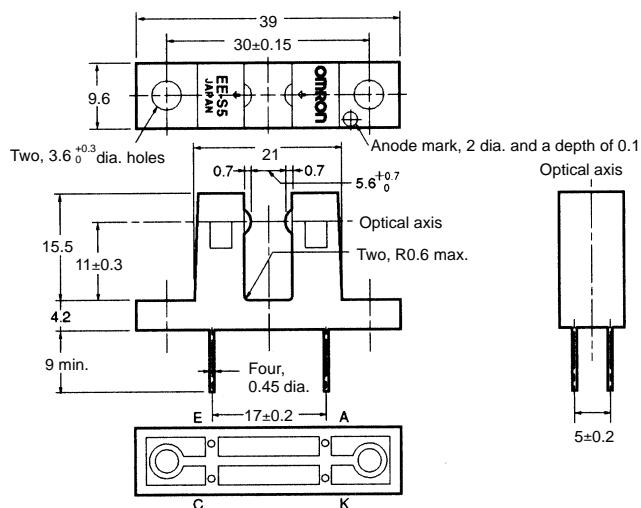
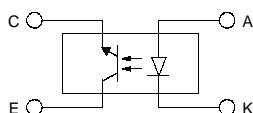


## ■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



### Internal Circuit



Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	$\pm 0.3$
$3 < \text{mm} \leq 6$	$\pm 0.375$
$6 < \text{mm} \leq 10$	$\pm 0.45$
$10 < \text{mm} \leq 18$	$\pm 0.55$
$18 < \text{mm} \leq 30$	$\pm 0.65$

Terminal No.	Name
A	Anode
K	Cathode
C	Collector
E	Emitter

## ■ Features

- High-sensitivity model with a wide slot.
- PCB mounting type.

## ■ Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rated value
Emitter	Forward current	I <sub>F</sub> 80 mA (see note 1)
	Pulse forward current	I <sub>FP</sub> ---
	Reverse voltage	V <sub>R</sub> 4 V
Receiver	Collector-Emitter voltage	V <sub>CEO</sub> 30 V
	Emitter-Collector voltage	V <sub>ECO</sub> ---
	Collector current	I <sub>C</sub> 30 mA
	Collector dissipation	P <sub>C</sub> 75 mW (see note 1)
Ambient temperature	Operating	T <sub>opr</sub> -20°C to 60°C
	Storage	T <sub>stg</sub> -20°C to 80°C
Soldering temperature	T <sub>sol</sub>	260°C (see note 3)

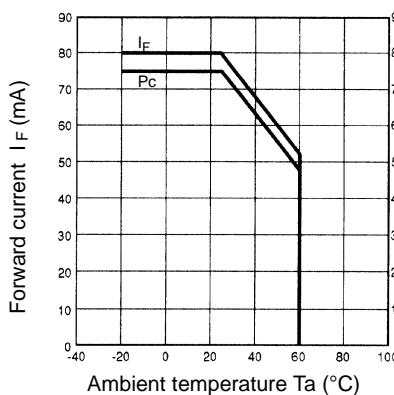
- Note:
- Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
  - The pulse width is 10  $\mu\text{s}$  maximum with a frequency of 100 Hz.
  - Complete soldering within 10 seconds.

## ■ Electrical and Optical Characteristics (Ta = 25°C)

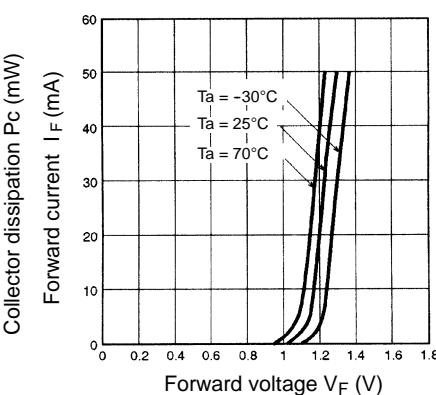
Item	Symbol	Value	Condition
Emitter	Forward voltage	V <sub>F</sub> 1.2 V typ., 1.5 V max.	I <sub>F</sub> = 40 mA
	Reverse current	I <sub>R</sub> 0.01 $\mu\text{A}$ typ., 10 $\mu\text{A}$ max.	V <sub>R</sub> = 4 V
	Peak emission wavelength	$\lambda_P$ 950 nm typ.	I <sub>F</sub> = 20 mA
Receiver	Light current	I <sub>L</sub> 1.8 mA min., 7.0 mA typ.	I <sub>F</sub> = 30 mA, V <sub>CE</sub> = 10 V
	Dark current	I <sub>D</sub> 10 nA typ., 500 nA max.	V <sub>CE</sub> = 10 V, 0 $\ell\text{x}$
	Leakage current	I <sub>LEAK</sub> ---	---
	Collector-Emitter saturated voltage	V <sub>CE</sub> (sat)	I <sub>F</sub> = 30 mA, I <sub>L</sub> = 1 mA
	Peak spectral sensitivity wavelength	$\lambda_P$ 800 nm typ.	V <sub>CE</sub> = 10 V
Rising time	tr	100 $\mu\text{s}$ typ.	V <sub>CC</sub> = 10 V, R <sub>L</sub> = 10 k $\Omega$ , I <sub>L</sub> = 30 mA
Falling time	tf	400 $\mu\text{s}$ typ.	V <sub>CC</sub> = 10 V, R <sub>L</sub> = 10 k $\Omega$ , I <sub>L</sub> = 30 mA

## ■ Engineering Data

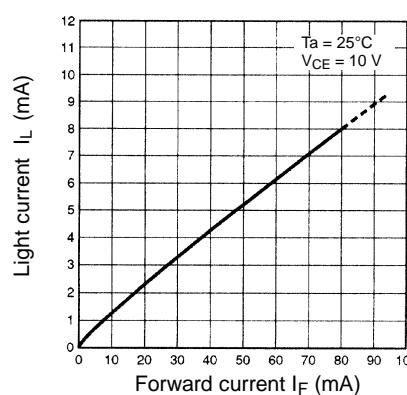
**Forward Current vs. Collector Dissipation Temperature Rating**



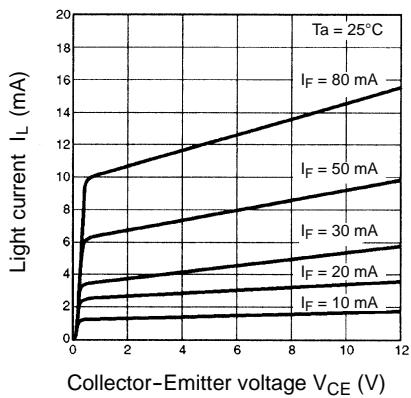
**Forward Current vs. Forward Voltage Characteristics (Typical)**



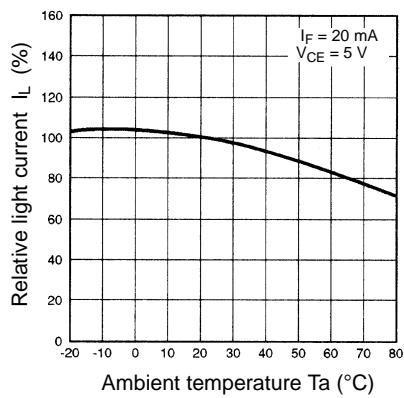
**Light Current vs. Forward Current Characteristics (Typical)**



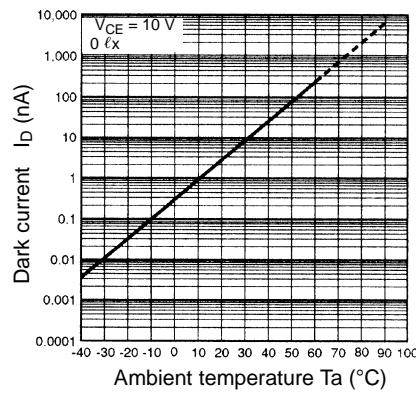
**Light Current vs. Collector-Emitter Voltage Characteristics (Typical)**



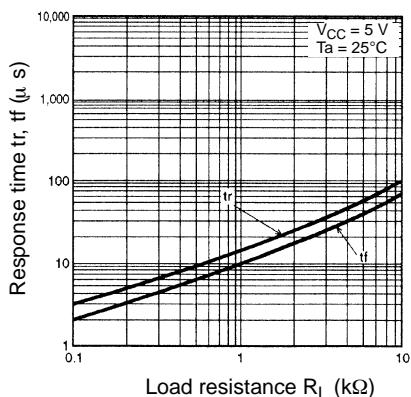
**Relative Light Current vs. Ambient Temperature Characteristics (Typical)**



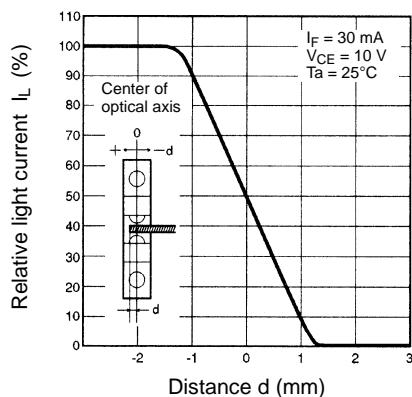
**Dark Current vs. Ambient Temperature Characteristics (Typical)**



**Response Time vs. Load Resistance Characteristics (Typical)**



**Sensing Position Characteristics (Typical)**



**Response Time Measurement Circuit**

